



CHENMKO ENTERPRISE CO.,LTD

SURFACE MOUNT

Dual N-Channel Enhancement Mode Field Effect Transistor

VOLTAGE 20 Volts CURRENT 7 Ampere

CHM8208JPT

Lead free devices

APPLICATION

- * Servo motor control.
- * Power MOSFET gate drivers.
- * Other switching applications.

FEATURE

- * Small flat package. (SO-8)
- * High density cell design for extremely low $R_{DS(ON)}$.
- * Rugged and reliable.
- * High saturation current capability.

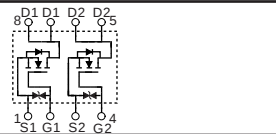
CONSTRUCTION

- * N-Channel Enhancement

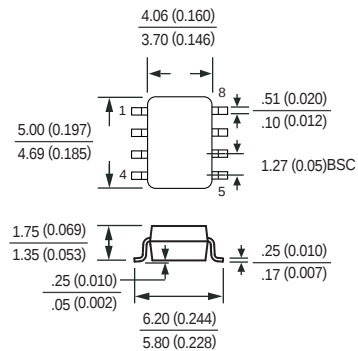


SO-8

CIRCUIT



www.DataSheet4U.com



Dimensions in millimeters

SO-8

Absolute Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	CHM8208JPT	Units
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	± 12	V
I_D	Maximum Drain Current - Continuous	7	A
	- Pulsed (Note 3)	25	A
P_D	Maximum Power Dissipation	2000	mW
T_J	Operating Temperature Range	-55 to 150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$

Note : 1. Surface Mounted on FR4 Board , $t \leq 10\text{sec}$
2. Pulse Test , Pulse width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$
3. Repetitive Rating , Pulse width limited by maximum junction temperature
4. Guaranteed by design , not subject to production trsting

Thermal characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1)	62.5	$^\circ\text{C/W}$
-----------------	--	------	--------------------

2007-11

RATING CHARACTERISTIC CURVES (CHM8208JPT)

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Conditions	Min	Typ	Max	Units
--------	-----------	------------	-----	-----	-----	-------

OFF CHARACTERISTICS

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	30			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}$			1	μA
I_{GSSF}	Gate-Body Leakage	$V_{GS} = 12\text{ V}, V_{DS} = 0\text{ V}$			+10	nA
I_{GSSR}	Gate-Body Leakage	$V_{GS} = -12\text{ V}, V_{DS} = 0\text{ V}$			-10	nA

ON CHARACTERISTICS (Note 2)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	0.5		1.2	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS}=4.5\text{ V}, I_D=7\text{ A}$		18	22	$\text{m}\Omega$
		$V_{GS}=2.5\text{ V}, I_D=5.6\text{ A}$		24	32	

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$		40		pF
C_{oss}	Output Capacitance			115		
C_{rss}	Reverse Transfer Capacitance			15		

SWITCHING CHARACTERISTICS (Note 4)

Q_g	Total Gate Charge	$V_{DS}=10\text{ V}, I_D=7\text{ A}$ $V_{GS}=4.5\text{ V}$		4.2	5.6	nC
Q_{gs}	Gate-Source Charge			1.0		
Q_{gd}	Gate-Drain Charge			2.4		
t_{on}	Turn-On Time	$V_{DD} = 10\text{ V}$ $I_D = 1\text{ A}, V_{GS} = 4.5\text{ V}$ $R_{GEN} = 6\text{ }\Omega$		0.34	0.68	μS
t_r	Rise Time			0.68	1.72	
t_{off}	Turn-Off Time			3.58	7.16	
t_f	Fall Time			2	4	

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS

I_S	Drain-Source Diode Forward Current	(Note 1)			7	A
V_{SD}	Drain-Source Diode Forward Voltage	$I_S = 7\text{ A}, V_{GS} = 0\text{ V}$ (Note 2)			1.2	V

RATING CHARACTERISTIC CURVES (CHM8208JPT)

Typical Electrical Characteristics

Figure 1. Output Characteristics

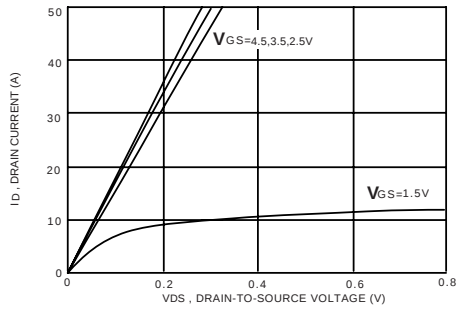


Figure 2. Transfer Characteristics

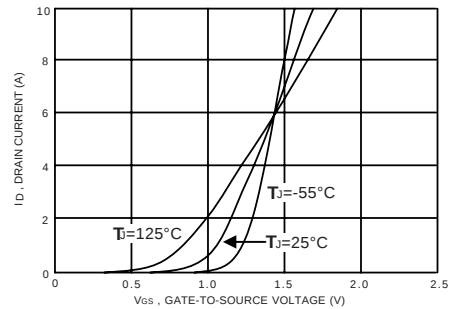


Figure 3. Gate Charge

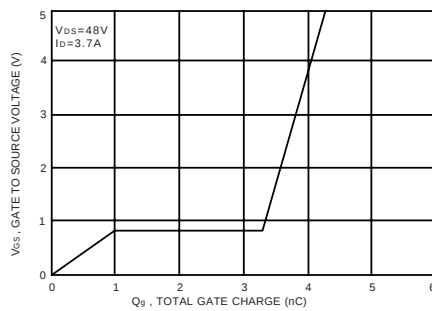


Figure 4. On-Resistance Variation with Temperature

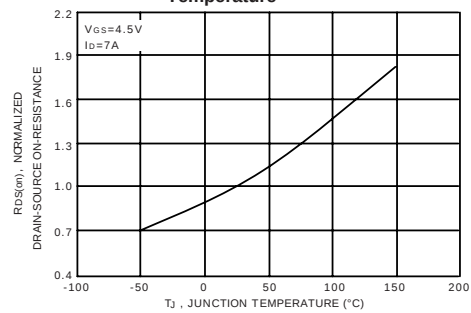


Figure 5. Gate Threshold Variation with Temperature

